

Total No. of Questions :4]

P5

SEAT No. :

[Total No. of Pages : 1

FE/Insem/APR-5

F.E. (Semester - II)

104010 : BASIC ELECTRONICS ENGINEERING

(2019 Pattern)

Time : 1 Hour]

Instructions to the candidates:

- 1) Answer Q.1 or Q.2, Q.3 or Q.4.
- 2) Assume suitable data if necessary.

[Max. Marks : 30

- Q1)** a) What is extrinsic semiconductor. Explain P-type & N-type semiconductor. [5]
- b) Draw and Explain Half Wave Rectifier (HWR) with its corresponding input and output waveforms. [5]
- c) Compare LED and Photodiode. [5]

OR

- Q2)** a) Define active and passive components Explain them with suitable examples. [5]
- b) For full wave bridge rectifier applied input voltage is $5\sin \omega t$. Calculate average output voltage, RMS voltage and PIV rating of diode used. [5]
- c) Explain V-I characteristics of zener diode. [5]

- Q3)** a) Draw and explain output characteristics of BJT in common emitter configuration. Show different regions of operation. [5]
- b) Draw and explain MOSFET as a switch. [5]
- c) For a Non - Inverting amplifier using op-amp if $R_f = 20k\Omega$ and $R_i = 1k\Omega$, $V_{cc} = \pm 15V$. Calculate Output voltage for $v_{in} = 3V$ and comment on the result. [5]

OR

- Q4)** a) Define transistor. Mention its types. For BJT, if $I_B = 20\mu A$ and $I_E = 2MA$. Calculate value of I_C and β (Beta). [5]
- b) Draw and Explain the drain characteristics of N-channel EMOSFET. Show the different regions of operation on the characteristics. [5]
- c) Draw and explain functional block diagram of operational amplifier (op-amp). [5]

